

Schottky Barrier Rectifier

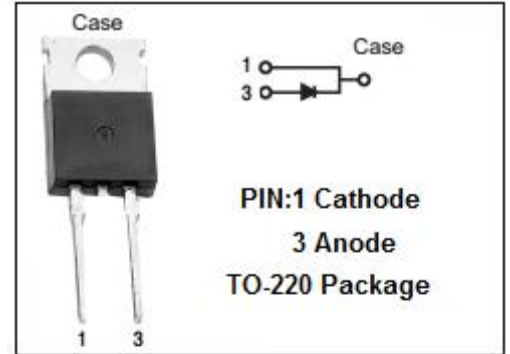
SBL845

FEATURES

- Schottky barrier chip
- Low Power Loss, High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

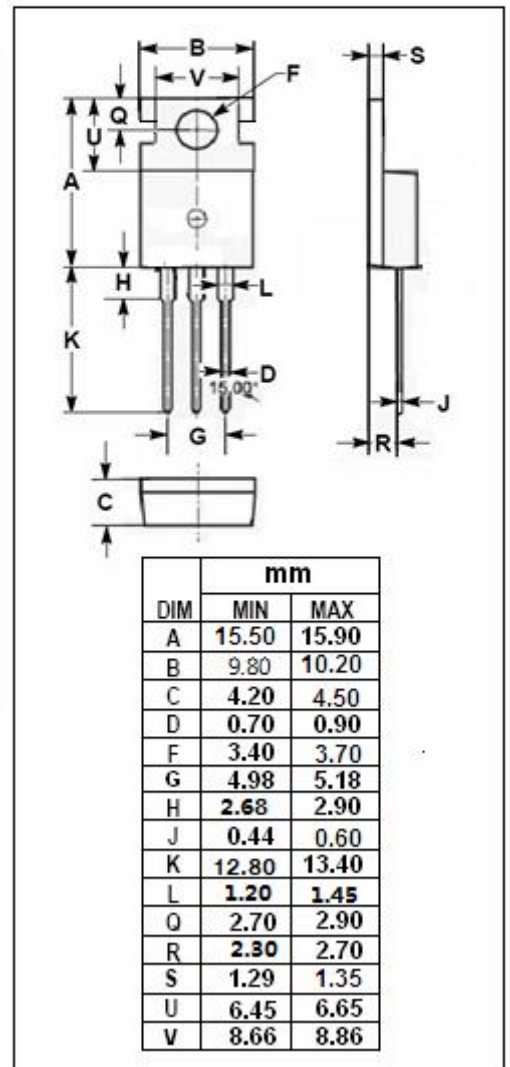
APPLICATIONS

- For use in low voltage ,high frequency inverters,free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RMS} V _R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	45	V
I _{F(AV)}	Average Rectified Forward Current	8	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	200	A
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-40~150	°C



Schottky Barrier Rectifier**SBL845****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6.9	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 8A ; T_j = 25^{\circ}C$	0.7	V
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}; T_j = 25^{\circ}C$	0.5	mA
		$V_R = V_{RWM}; T_j = 100^{\circ}C$	50	mA

Downloaded from Alldatasheet.com